SF2001G thru SF2008G

Pb Free Plating Product

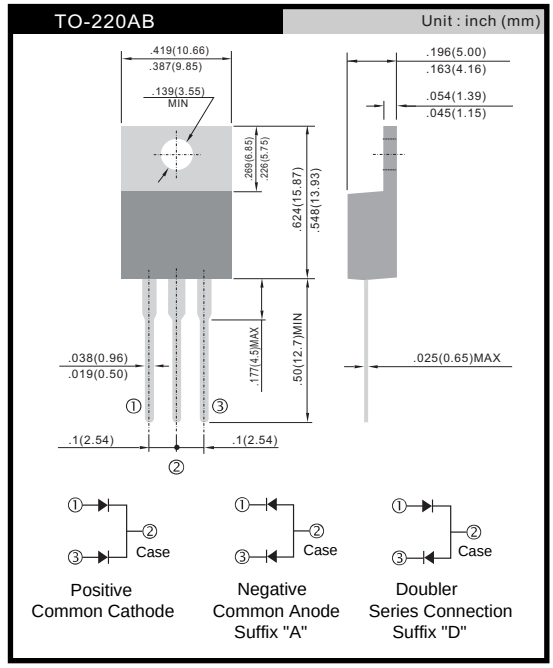
20.0 Ampere Dual Unipolar-Doubler Polarity Superfast Recovery Diode

Features

- ✶ Fast switching for high efficiency
- ✶ Low forward voltage drop
- ✶ High current capability
- ✶ Low reverse leakage current
- ✶ High surge current capability

Mechanical Data

- ✶ Case: TO-220AB Heatsink
- ✶ Epoxy: UL 94V-0 rate flame retardant
- ✶ Terminals: Solderable per MIL-STD-202 method 208
- ✶ Polarity: As marked on body
- ✶ Mounting position: Any
- ✶ Weight: 2.24 gram approximately



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Common Cathode Common Anode Suffix "A" Anode and Cathode Coexistence Suffix "D"	SYMBOL	SF2001G SF2001GA SF2001GD	SF2002G SF2002GA SF2002GD	SF2004G SF2004GA SF2004GD	SF2005G SF2005GA SF2005GD	SF2006G SF2006GA SF2006GD	SF2008G SF2008GA SF2008GD	UNIT
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	V
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	V
Maximum Average Forward Rectified Current T_C=125°C	$I_{F(AV)}$	20.0						A
Peak Forward Surge Current, 8.3ms single Half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	200			175			A
Maximum Instantaneous Forward Voltage @ 10.0 A	V_F	0.975			1.3		1.5	V
Maximum DC Reverse Current @T_J=25°C At Rated DC Blocking Voltage @T_J=125°C	I_R	10.0 250						uA uA
Maximum Reverse Recovery Time (Note 1)	Trr	35						nS
Typical junction Capacitance (Note 2)	C_J	120			70			pF
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150						°C

NOTES : (1) Reverse recovery test conditions I_F = 0.5A, I_R = 1.0A, Irr = 0.25A.

(2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts DC.

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FIG.1 - FORWARD CURRENT DERATING CURVE

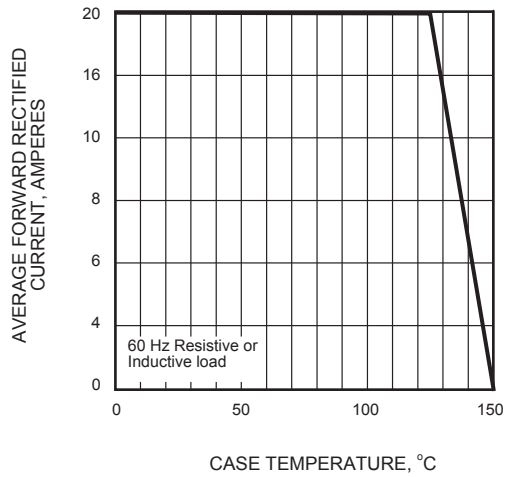


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

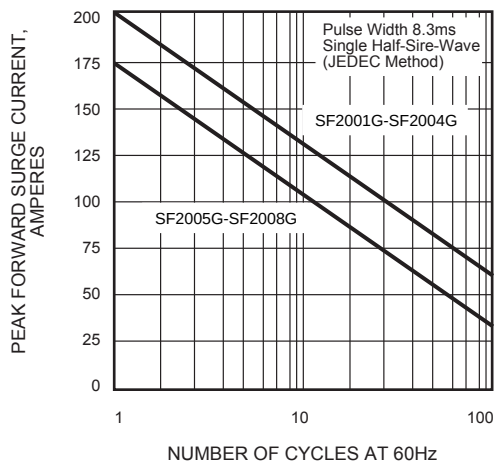


FIG.3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

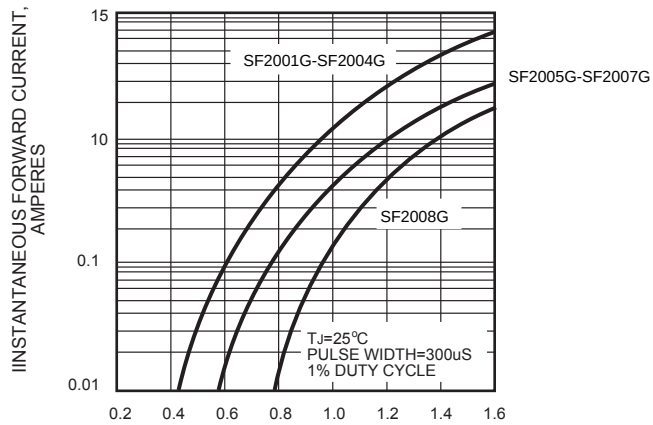


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

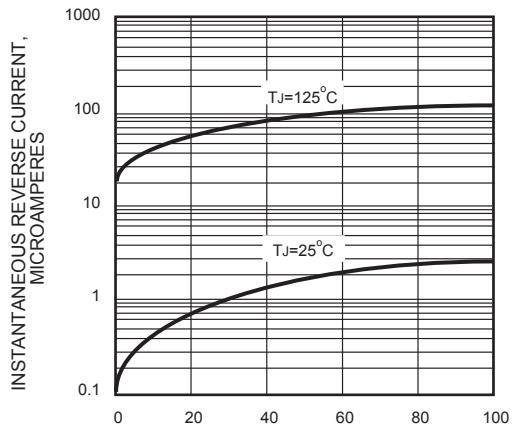
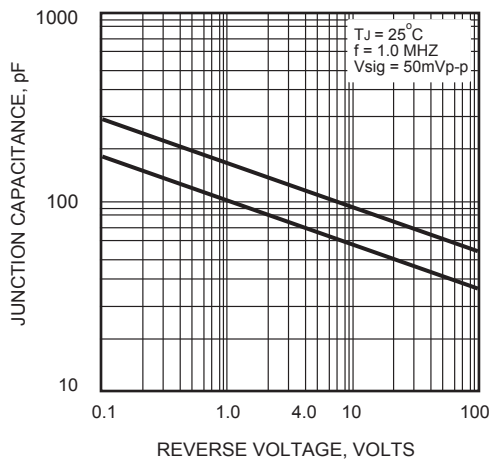


FIG.5 - TYPICAL JUNCTION CAPACITANCE



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